

SuperMOS –SOT-23 30V BV_{DSS} , 40m Ω $R_{DS(ON)}$, I_D N-channel MOSFET

1. Description

The AO3402A-ES is N-Channel enhancement MOS Field Effect Transistor. Uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. Device is suitable for use in DC-DC conversion, power switch and charging circuit. Standard Product AO3402A-ES is Pb-free.

2. Features

- 30V, $R_{DS(ON)}=40m\Omega$ (Typ.) @ $V_{GS}=10V$
 $R_{DS(ON)}=43m\Omega$ (Typ.) @ $V_{GS}=4.5V$
 $R_{DS(ON)}=55m\Omega$ (Typ.) @ $V_{GS}=2.5V$
- High density cell design for low $R_{DS(on)}$
- Material: Halogen free
- Reliable and rugged
- Avalanche Rated
- Low leakage current

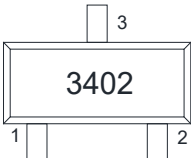
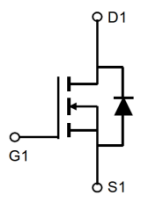
3. Applications

- PWM applications
- Load switch
- Power management in portable/desktop PCs
- DC/DC conversion

4. Ordering Information

Part Number	Package	Marking	Material	Packing	Quantity per Reel	Flammability Rating	Reel Sizes
AO3402A-ES	SOT-23	3402	Halogen free	Tape & Reel	3,000 PCS	UL 94V-0	7 inches

5. Pin Configuration and Functions

Pin	Function	Outline	Circuit Diagram
1	Gate		
2	Source		
3	Drain		

6. Specification

Absolute Maximum Rating & Thermal Characteristics

Ratings at 25 °C ambient temperature unless otherwise specified.

Parameter		Symbol	Limit	Unit
Drain-Source Voltage		BV_{DSS}	30	V
Gate-Source Voltage		V_{GS}	± 12	V
Continuous Drain Current	$T_A=25^{\circ}\text{C}$	I_D	4.2	A
	$T_A=75^{\circ}\text{C}$		3.3	
Maximum Power Dissipation		P_D	1.4	W
Pulsed Drain Current		I_{DM}	15.6	A
Operating Junction Temperature		T_J	150	$^{\circ}\text{C}$
Lead Temperature		T_L	260	$^{\circ}\text{C}$
Storage Temperature Range		T_{stg}	-55 to 150	$^{\circ}\text{C}$

Thermal resistance ratings

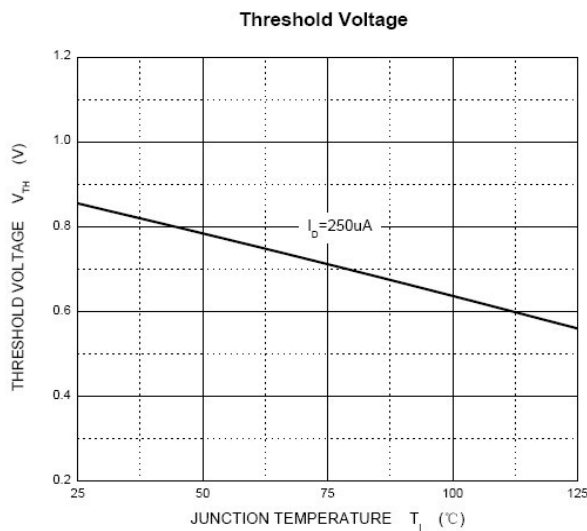
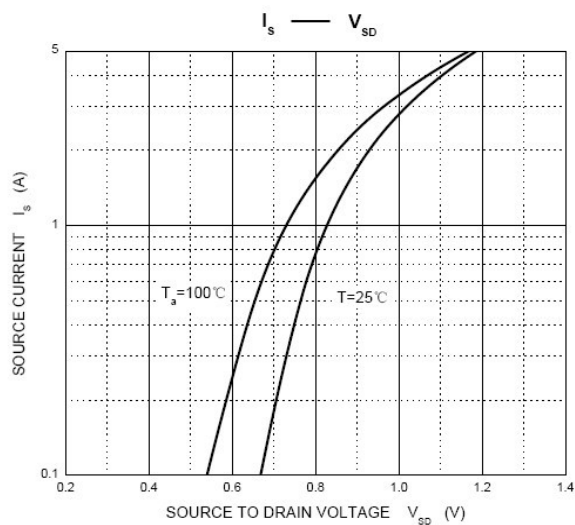
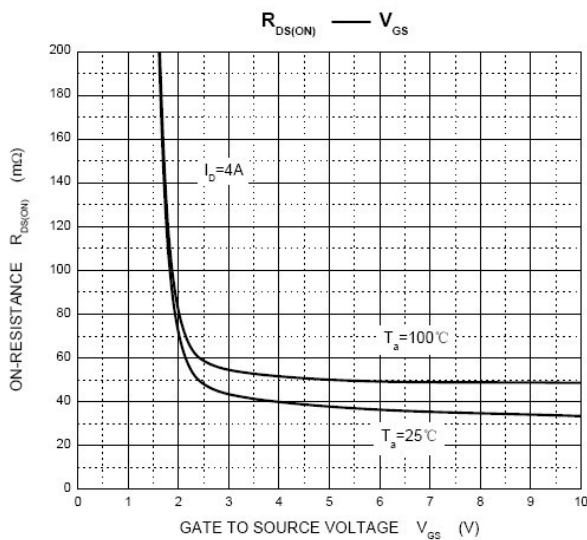
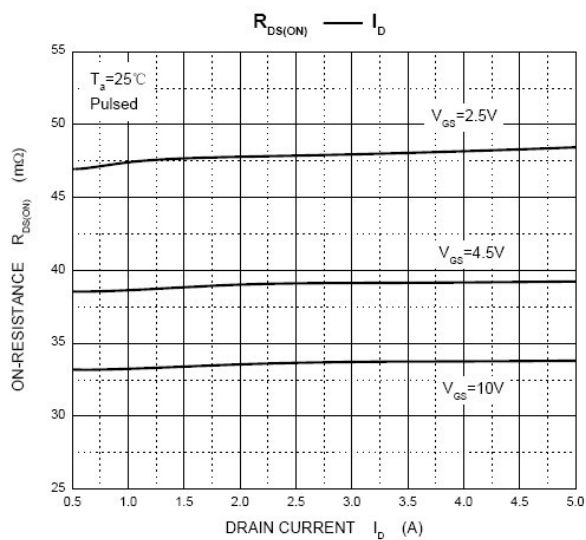
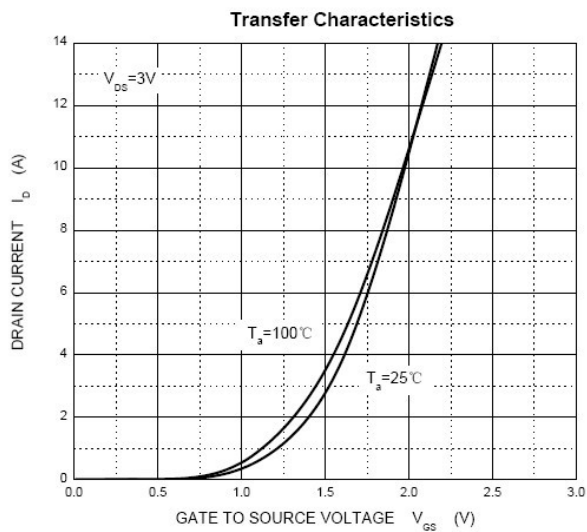
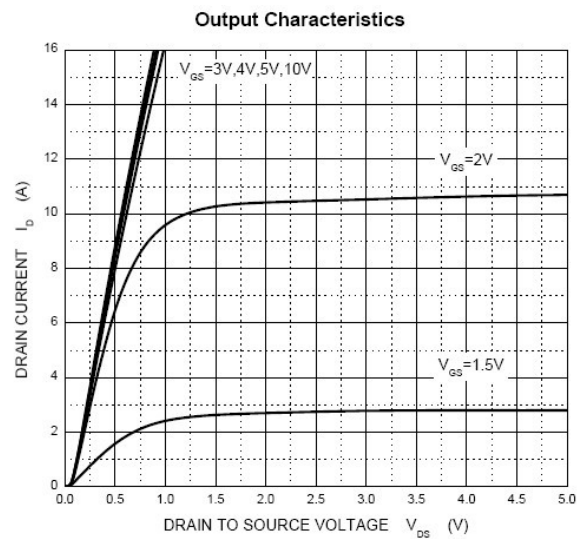
Single Operation				
Parameter	Symbol	Typical	Maximum	Unit
Junction-to-Ambient Thermal Resistance	$R_{\theta JA}$		90	$^{\circ}\text{C/W}$

Electrical Characteristics

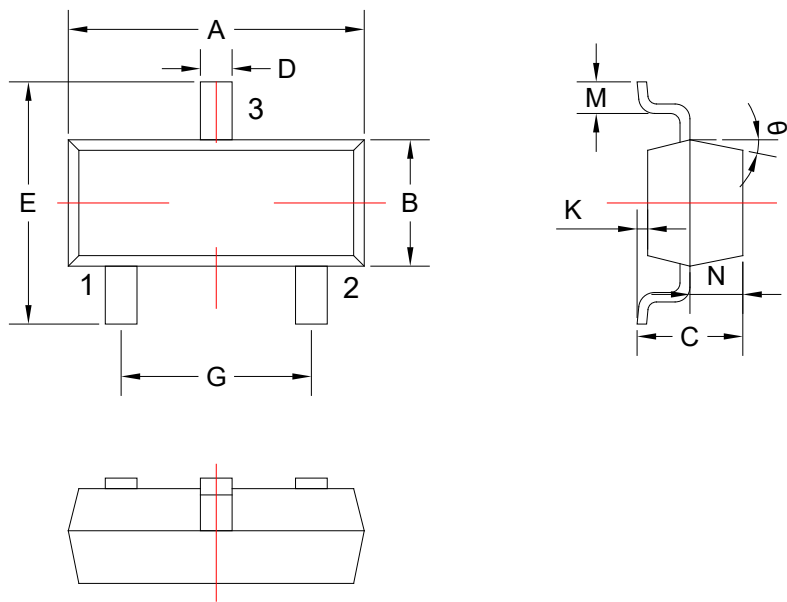
At TA = 25°C unless otherwise specified

Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
OFF CHARACTERISTICS						
Drain-to-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V, I _D =250uA	30			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =30V, V _{GS} =0V			1	uA
Gate-to-source Leakage Current	I _{GSS}	V _{DS} =0V, V _{GS} =±12V			±100	nA
ON CHARACTERISTICS						
Gate Threshold Voltage	V _{GS(TH)}	V _{GS} =V _{DS} , I _D =250uA	0.6	0.9	1.5	V
Drain-to-source On-resistance	R _{DS(on)}	V _{GS} =10V, I _D =3.6A		40	51	mΩ
		V _{GS} =4.5V, I _D =2A		43	54	
		V _{GS} =2.5V, I _D =1A		55	69	
Forward transconductance	g _{fs}	V _{DS} =5V, I _D =3.6A			40	S
CHARGES, CAPACITANCES AND GATE RESISTANCE						
Input Capacitance	C _{ISS}	V _{GS} =0V, f=1MHz, V _{DS} =15V		390		pF
Output Capacitance	C _{OSS}			55		
Reverse Transfer Capacitance	C _{RSS}			41		
Total Gate Charge	Q _{G(TOT)}	V _{GS} =10V, V _{DS} =15V, I _D =3.6A		4.4		nC
Gate-to-Source Charge	Q _{GS}			0.6		
Gate-to-Drain Charge	Q _{GD}			1.4		
SWITCHING CHARACTERISTICS						
Turn-On Delay Time	t _{d(ON)}	V _{GS} =10V, V _{DS} =15V, RL=3.5Ω, RG=6Ω		3.3		ns
Rise Time	t _r			1		
Turn-Off Delay Time	t _{d(OFF)}			21.7		
Fall Time	t _f			2.1		
BODY DIODE CHARACTERISTICS						
Forward Voltage	V _{SD}	V _{GS} =0V, I _S =3.6A			1.5	V

7. Typical Characteristic



8. Dimension (SOT-23)



COMMON DIMENSIONS CUNITS MEASURE=MILLIMETER					
SYMBOL	MIN	MAX	SYMBOL	MIN	MAX
A	2.85	3.04	G	1.80	2.00
B	1.20	1.40	K	0	0.10
C	0.90	1.10	M	0.20	-
D	0.40	0.50	N	0.50	0.70
E	2.25	2.55	θ	5°	9°

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